

# **Conference Agenda**

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Symposium IX: Design and Automation of Circuits and Systems	31
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## PLENARY SESSION

## **Distinguished Conference Keynote Speakers**











Dr. Giorgio Allegato

**MEMS Technology** 

and Sensor Group,

STMicroelectronics,

**R&D Director, MEMS** 

Dr. Peng Bai

Semiconductor,

CEO

Rong

China

Emeritus Professor of Electronic Engineering, Cambridge University,

Prof. John Robertson

UK

Dr. Michael Chudzik

VP of Technology, IMS ICAPS &Packaging,

Applied Materials, US

Prof. Tobias Delbruck

Professor in
Neuromorphic
Engineering,
Institute of

Neuroinformatics, Switzerland

Italy

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Sunday, March 17, 2024

Meeting Room: 3rd Floor Auditorium

08:15-08:45 Registration

08:45-09:15 Opening Ceremony

**Opening Remarks by Conference Chair** 

Opening Remarks by SEMI

Presentation of the Best Student Paper Awards and the Best Young Engineer Paper Awards

09:15-09:50 Evolution of Moore's Law: a Perspective

Dr. Peng Bai

CEO, Rong Semiconductor, China

09:50-10:25 New Materials vs New Geometries in Electronic Devices

Prof. John Robertson

Emeritus Professor of Electronic Engineering, Cambridge University, UK

10:25–11:00 Integrated Module Approach to Solutions in the Specialty Device Market

Dr. Michael Chudzik

VP of Technology, IMS ICAPS & Packaging, Applied Materials, USA

11:00–11:35 50 Years of Silicon Retina History

Prof. Tobias Delbruck

Professor in Neuromorphic Engineering, Institute of Neuroinformatics, Switzerland

11:35–12:10 MEMS - Sustainable Technologies for a Sustainable World

Dr. Giorgio Allegato

MEMS Technology R&D Director, MEMS and Sensor Group, STMicroelectronics, Italy

**Panel Discussion** 

Sunday, March 17, 2024

Meeting Room: 3rd Floor Yellow River Hall

17:05-18:15 Al for IC Design & Manufacturing: The Hopes, Challenges, and Opportunities

Moderator: Prof. Cheng Zhuo, Zhejiang University

Panelists: Prof. Daniele Ielmini, Politecnico Di Milano; Dr. Jun Yuan, Qualcomm;

Prof. Yu Wang, Tsinghua University; Prof. Runsheng Wang, Peking University;

Mr. Zusheng Yang, Empyrean

## Symposium I: Device Engineering and Memory Technology

Sunday, March 17, 2024 Shanghai International Convention Center

Meeting Room: 3rd Floor Yellow River Hall

Session I: In-memory Computing I

Session Chair: Hao Cai

\*13:30-13:55 Implementation of Spintronic MRAM Circuits and Systems Hao Cai, Southeast University \*13:55-14:20 Defect tolerant physics-inspired computing in memristor arrays Can Li, University of Hong Kong Multifunctional RRAM Chip with Configurability for Sparsity-aware In-memory Isng 14:20-14:35 Machine Wenshuo Yue, Peking University 14:35-14:50 A method of scalable polysilicon resistor by adjusting shielding metal in CMOS process Hunjin Lee, X-FAB A 110nm BCD-on-SOI Technology offering Best-In-Class Nonvolatile Memory IP for 14:50-15:05 **Automotive Application** 

Session II: In-memory Computing II

Session Chair: Xin Si

15:05-15:20

\*15:20-15:45 2D devices and in-sensor computing
Feng Miao, Nanjing University

**Coffee Break** 

\*15:45-16:10 SRAM based Compute-in-Memory Circuits Design for CNN and Transformers

Xin Si, Southeast University

\*16:10-16:35 All-dielectric metasurfaces for vortex generation and Detection

Shumin Xiao, Harbin Institute of Technology

Boon Jiew Chee, X-FAB Sarawak Sdn. Bhd.

16:35-16:50 Analog Device Engineering and Enhancement in 0.18um BCD on SOI Technology

**Platform** 

Poh Ching Sim, X-FAB Sarawak Sdn. Bhd.

16:50-17:05 Innovative Test Solution Design and Production Practices for Automotive Based on

**ADVANTEST 93K** 

Jibao Fan, Advantest (China) Co., Ltd.

Monday, March 18, 2024 Shanghai International Convention Center

Meeting Room: 3rd Floor Yellow River Hall

**Session III: Emerging Computing Technologies** 

Session Chair: Hao Wang

\*08:30-08:55 2D Material Devices for Advanced Computing

Han Wang, University of Hong Kong

\*08:55-09:20 A Full Spectrum of Computing-In-Memory Technologies

Zhong Sun, Peking University

09:20-09:35 Inflection Points in CFET Scaling: Impact of DTCO Boosters

Dmitry Yakimets, Huawei Technologies R&D Belgium

09:35-09:50 Ultrathin TiO<sub>2</sub> channel HfLaO FeFET with Low Operation Voltage

Xujin Song, Peking University

Session IV: Memory Devices I

Session Chair: Jianshi Tang				
	*10:05-10:30	Enhance Chip Connectivity and Functionality through RRAM-based Monolithic 3D Integration		
		Jianshi Tang, Tsinghua University		
	*10:30-10:55	Single Element Switch		
		Min Zhu, Shanghai Institute of Microsystem and Information Technology		
	10:55-11:10	First Principle Study on Oxygen Vacancy Induced Ferroelectricity in HfO <sub>2</sub> -based ferroelectrics		
		Chenxi Yu, Peking University		
	11:10-11:25	Low Frequency Noise and Hot Carrier Degradation Characteristics on 55nm LP Platform		
		Gang Wang, Hangzhou HFC Semiconductor Corporation		
	11:25-13:30	Lunch Break		

Session V: Emerging Devices

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Session	Chair	( an	
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dession onan Li		
13:30-13:45	A Novel Ultralow Voltage Slope Device	
	Pengtao Li, Zhejiang University	
13:45-14:00	Experimental Investigation of Polarization Switching Speed in Ferroelectric HfO₂ for High-Speed and Low-Power Applications	
	Hao Zheng, Peking University	
14:00-14:15	A Novel Hybrid-Channel Gate-All-Around Nanosheet Transistor For Leakage Control And Subthreshold Slope Reduction	
	Yumin Xu, Fudan University	
14:15-14:30	Investigation of Self-Heating Effect on Forksheet Field-Effect Transistors	
	Pan Zhao, Peking University	
14:30-14:45	Coffee Break	

Session VI: Memory Devices II Session Chair: Kechao Tang

occording that the state of the				
*14:45-15:10	High endurance field-effect transistor memory based on Hafnium-oxide ferroelectrics			
15:10-15:25	Kechao Tang, Peking University Interface Treatment of Epitaxial Si FinFET Channel in Replace Metal Gate with Simultaneously Performance Improvement and Leakage Reduction Renjie Jiang, Institute of Microelectronics of the Chinese Academy of Sciences			
15:25-15:40	Experimental Investigation on the Back Gate Modulation of Extra-Thin Body pMOSFETs			
15:40-15:55	Rui Su, Zhejiang University Impact Of Thickness Dependent Ferroelectric And Interface Charge Variation On Device- To-Device Variation In Ferroelectric FET Fan Zhang, Xidian University/ IMECAS			

### **Poster Session:**

Yield Improvement in 4X Node Technology ETOX NOR-flash by Optimizing Control Gate Related Process and Design

Yihang Du, Huahong Semiconductor (WUXI) Limited

## Machine Learning-based Performance Prediction Model Optimization for SOI LDMOS Using Adaptive Small Space Dataset

Jinwen You, Nanjing University of Posts and Telecommunications

**HBM Device Test & Repair Solution on T5833** 

Xiang Ling, Advantest (China) Co., Ltd.

## SUBSTRATE CURRENT IMPROVEMENT AND INVESTIGATION IN LOW VOLTAGE POWER LDMOS WITH A NOVEL DESIGN

Zhaozhao Xu, Huahong Semiconductor (Wuxi) Limited

**Short-Loop Method to Shorten Gate Process Characterization Cycle Time** 

Bing Li, HangZhou HFC Semiconductor Corp.

**Enhancement of SRAM Read and Write Noise Margin by Device Performance Adjustment** 

Ailin Li, Semiconductor Manufacturing North China (Beijing) Corporation (SMNC)

FABRICATION PROCESS IMPROVEMENT OF AGGRESSIVELY SCALED DUAL-BIT/CELL SPLIT-GATE FLOATING-GATE FLASH CELL

Yintong Zhang, Huahong Semiconductor (Wuxi) Limited

STI Gap-Filling Performance Improvement by the Process Integration Optimization in the 4Xnm ETOX Nor Flash

Zhuangzhuang Wang, Hua Hong Semiconductor (Wuxi) Limited

Breakdown Voltage Improvement of LDMOS by CESL Optimization in High-Voltage 90 nm BCD Technology

Ye Tian, Huahong Semiconductor (Wuxi) Limited

Research on the substitution of MIM capacitors and MOM capacitors on power devices

Wenwu Zhu, Huahong Semiconductor(Wuxi)

STUDY ON DNW PERFORMANCE IN 55NM CMOS

HAOQI ZHENG, Semiconductor Manufacturing International Corporation

STUDY ON NIPT SALICIDE WITH VARIOUS PLATINUM PERCENTAGE PERFORMANCE

HAOQI ZHENG, Semiconductor Manufacturing International Corporation

Anomalous Hot carrier injection induced degradation of drain current in HVMOS with STI Bocheng Zhao, Shanghai University

Study of Improvement for substrate current in High-Voltage NMOS with Shallow Trench Isolation

Bocheng Zhao, Shanghai University

The Effect of Depth, Air Gap Width and Ion Implant on Deep Trench Isolation for BCD Technology

Chen Chen, Huahong Wuxi Semiconductor Manufactory Co., Ltd.

A new method for improving 8V ESD performance

Chuang Wang, Shanghai Huali Microelectronics Corporation

Fabrication of Semi-enclosed Control Gate of Semi-Floating Gate Transistor

Shiling Yang, Shanghai Huali Integrated Circuit Corporation

Threshold Voltage Mismatch Dependence of SRAM Yield Window Simulation

Chun-Hsiung Wang, HFC Semiconductor

Optimization of the 8T SRAM bitcell design

Lu-Ping Wu, HFC Semiconductor

**SRAM Device Threshold Voltage Mismatch Investigation and Improvement** 

Chun-Hsiung Wang, HFC Semiconductor

Effect of lightly doped drain doping on variability for static random-access memory

Qiao Teng, Zhejiang University

## Improvement of NLDMOS Performance in Low-Resistivity Substrate for Integration with Discrete Power Devices on One Chip

Yuncong Chen, HuaHong Grace Semiconductor Manufacturing Corporation

A photoelectric memristive devices for Artificial visual perception

Xuemeng Fan, Zhejiang University

Al<sub>2</sub>O<sub>3</sub>/AlOx Memristor with Nearly Ideal Synaptic Characteristics

Qian He, Zhejiang University

Two-Dimensional MoS<sub>2</sub> Based Memristors For Artificial Neural Network

Hailiang Wang, Zhejiang University

A Novel RRAM-Based TCAM Search Array

Zhen Wang, Zhejiang University

Static leakage failure analysis and improvement for small size SRAM

Minghui Zhu, Shanghai Huali Microelectronics Corporation

The Modeling and optimization of the Polysilicon Gate Line Width Roughness for Improving the Performance of 55nm CMOS devices

Yaoting Wang, Zhejiang University

Hot-Carrier-Induced Degradations and Optimizations for Lateral DMOS Transistor with Shallow Trench Isolation and Step Oxide Improvement

Zhibo Liu, Huahong Wuxi Semiconductor Manufactory

Virtual Fab Semiconductor Process Modeling Augmented Vertical Gate All Around Complementary FET based 6T SRAM path-finding

Zhaohai Di, Institute of Microelectronics, Chinese Academy of Sciences

Novel Memtransistor-based LIF Neuron with Tunable Ionic Dynamics for Spiking Neural Networks

Zhen Yang, Peking University

Ultra-low operating voltage RRAM devices regulated by nitride insertion layers

Zijian Wang, Zhejiang university

New Insight into Impacts from Read Cycle Number and Voltage Sweeping Direction on Memory Window of Ferroelectric FET

Chang Su, Peking University

IGZO-Ta2O5 Dual-layer CBRRAM: A Low Voltage and High Switching Ratio Storage Solution

Shengpeng Xing, Zhejiang University

The Optimization of the specific on-resistance of the VDMOS on the integrated platform of VDMOS and LDMOS

Xiaoqing Cai, HuaHong Grace Semiconductor Manufacturing Corporation

A STUDY OF PARASITIC CAPACITANCE SIMULATION IN DRAM BY VIRTUAL FABRICATION

Dempsey Deng, Lam Research

Benefits of Applied VSE High Current Implanters for White Pixel Reduction in Image Sensors

Shasha Wang, Applied Materials

Leakage Reduction Evolution With Gate Oxide Scaling

Yongchun Xuan, Applied Materials

Cost Effective Low Temperature Annealing Achieved by Producer Pyra

Yang Liu, Applied Materials

Advanced Ion Implanter with Metal Reduction Kit (MRK) for CIS White Pixel Improvement

Kui Shi, Applied Materials

Device performance (leakage & Rc) improvement by Trident XP CrionTM

Yuhang Jin, Applied Materials

## **Effective Tuning Knobs for High Current Implant Uniformity Optimization**

Jinsong Lin, Applied Materials

Trident N/C co-implant for LDD dopant diffusion control

Zuoliang Han, Applied Materials

Solution-Processed Organic CMOS Inverter Via Contact Modulation

Jiarong Cao, Nanjing University of Posts and Telecommunications

**Ultra-Short Channel Polymer Transistors** 

Zhiqi Xu, Nanjing University of Posts and Telecommunications

Exploring Low-Frequency Noise Behavior in Vertically Structured Organic Schottky Photodiodes

Tingting Ji, Nanjing University of Posts and Telecommunications

Flexible Low-Voltage, Hysteresis-Free Ferroelectric Polymer Transistors

Yao Yu, Nanjing University of Posts and Telecommunications

A comprehensive solution to parse, compare, convert, and compile TST pattern Weilong Li, Teradyne

A Novel Approach for Doping Two-Dimensional MoS<sub>2</sub> Materials: ZnO Polar Interfacial Charge Transfer Method

Lijun Xu, Institute for Microelectronics, Chinese Academy of Science

Calculation Method of Target Erosion in the Planar DC Magnetron Sputtering

Jihua Ding, Beijing NAURA Microelectronics Equipment Co., Ltd.

## Symposium II: Lithography and Patterning

Sunday, March 17, 2024 Shanghai International Convention Center

Meeting Room: 3H+3I+3J

Session I: Lithograpy/Etch joint session (II & III)

Session Chairs: Leo Pang / Ying Zhang 13:30-13:35 Opening Remarks

\*\*13:35-14:05 How Process, Equipment, Material, Computation that work together to make up the

Performance of Photolithography

Qiang Wu, Fudan University

\*\*14:05-14:35 Novel Etch Solution with Sym3 for Logic BEOL Patterning Etch Applications

Hui Sun, Applied Materials

\*\*14:35-15:05 New Materials and New Functionalities Co-work scaling, and the Exploration of Inner

**Spacer Technique** 

David Xiao, Qianmo Micros Design LLC

15:05-15:20 Coffee Break

Session II: Developments in Lithography Session Chairs: Qiang Wu / George Lu

\*15:20-15:45 Recent progress of EUV Chemically Amplified Resist with Negative-Tone Development

(CAR-NTD) for improving Chemical Stochastic

Toru Fujimori, FUJIFILM Corporation

\*15:45-16:10 Acid Generation Efficiency Prediction by Bond Cleavage Calculation of EUV Photoacid

Generators

Jayoung Koo, DuPont

\*16:10-16:35 High-efficient nanofocusing for nanopattern with a plasmonic BNA

Dandan Han, University of Chinese Academy of Sciences

Monday, March 18, 2024 Shanghai International Convention Center

Meeting Room: 3H+3I+3J

Session III: Process, Equipment, and Materials I Session Chairs: Weiming Gao / Xiaoming Ma

\*\*08:30-09:00 From Tape to Mirrors: 50 Years of Progress in Photomask Technology

Chris Progler, Photronics

\*09:00-09:25 The Influence of Aberration on 193 Nm Immersion (193i) Lithography Process Window

Yanli Li, Fudan University

\*09:25-09:50 Polyimides for Power Device Applications

Masao Tomikawa, Toray Industries Inc.

09:50-10:05

10:05-10:20 Coffee Break

Session IV: Computational Lithography Session Chairs: Yayi Wei / Shiyuan Liu

\*10:20-10:45 Inverse lithography with adaptive mask complexity

Xiaoxuan Liu, Guangdong University of Technology

*11:10-11:35	Mask Corner Rounding in OPC Modeling
	Weimei Xie, National Integrated Circuit Innovation Center
11:35-11:50	A Study of the Via Pattern Lithography Process Window under the 7 nm Logic Design Rules with 193 nm Immersion Lithography
	Jinhao Zhu, Fudan University
11:50-13:30	Lunch Break

Session V: Next DTCO and Design Optimization Session Chairs: David Wei / Wenzhan Zhou *13:30-13:55  A Study of Flexible BEOL Design Rules Allowing Degreed Slanted Interconne Advanced Nodes				
	Xianhe Liu, Fudan University			
*13:55-14:20	Research on Cross-Level Interconnection of Metal Layers under 193 Immersion Lithography Conditions			
	Ying Li, National Integrated Circuit Innovation Center			
*14:20-14:45	A Study of the Minimum Area Rule under the 193 nm Immersion Lithography for Via and Cut Patterns			
	Qiang Wu, Fudan University			
14:45-15:00	Coffee Break			

Session VI: Process, Equipment, and Materials II Session Chairs: Wenzhan Zhou / Weiming Gao				
*15:00-15:25	The Spin-on Multi-Layer Material Status for Advanced Device			
	Satoshi Dei, JSR Electronic Materials (Shanghai)			
15:25-15:50				
*15:50-16:15	Enhancing High-throughput and High-precision CD-SEM Metrology Through Advanced Deep Learning-Based Image Processing Bo Wang, Hitachi High-Tech Corporation			
16:15-16:30	Correlation Between CD/LWR and Focus Level Fitting Error: A Process Quality Indicator			
	Tianhao Huang, Zhejiang University			
16:30-16:45	The Impact of Wafer Warpage-Induced Unevenness on Alignment			
	Pan Liu, Zhejiang University			

### **Poster Session:**

Pattern top loss improvement to enlarge process window for advanced node

Le Kuai, Nexchip Semiconductor Corporation

Coherence characterization for CDU budget breakdown in advanced DUV lithography

Wei Zhao, University of Chinese Academy of Sciences

Innovated Methodology Improving CD Uniformity for Lithography Using Wafer-less

**Dynamic Grouping Process Characteristics** 

Yong-Qiang Che, Semiconductor Manufacturing Beijing Corporation

## Symposium III: Dry &Wet Etch and Cleaning

Sunday, March 17, 2024 Shanghai International Convention Center

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Meeting Room: 3H+3I+3J

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Hui Sun, Applied Materials

\*14:35-15:05 New Materials and New Functionalities Co-work scaling, and the Exploration of Inner

**Spacer Technique** 

David Xiao, Qianmo Micros Design LLC

15:05-15:20 Coffee Break

Session II: Advanced Patterning

Meeting Room: 3C+3D

Session Chair: Qingjun Zhao

\*15:20-15:50 The New Developments in Etching of Dielectrics

Yuanwei Lin, Beijing NAURA Microelectronics Equipment Co., Ltd.

15:50-16:05 Study of tungsten-doped carbon hard mask etch using O<sub>2</sub>/NF<sub>3</sub> based chemistry

Li-Tian Xu, Beijing NAURA Microelectronics Equipment Co., Ltd.

16:05-16:20 Plasma Corrosion Resistant ALD Coatings for Semiconductor Manufacturing Process

Equipment

Lassi Leppilahti, Beneq

A Study on SADP Film Stack Selection for Line Roughness Improvement in Planar 1xnm

**NAND Flash** 

Yinan Ma, Semiconductor Manufacturing North China (Beijing) Corporation

16:35-16:50 A STUDY OF WAFER-LESS AUTO CLEAN EFFICIENCY PROMOTION METHOD IN DOUBLE

PATTERNING DIELECTRIC HARD MASK PROCESS

Xinruo Su, Semiconductor Manufacturing North China

16:50-17:05 Advanced Patterning Solutions for Logic and Memory Device Manufacturing

Taiyen Peng, Jiangsu Leuven Instruments Co., Ltd.

Monday, March 18, 2024 Shanghai International Convention Center

Meeting Room: 3C+3D

Session III: FEOL/MOL Etching Session Chair: Hai Cong

08:45-09:00 Challenge of boron-doped silicon hardmask etching

Xuehua Wang, Beijing NAURA Microelectronics Equipment Co., Ltd.

09:00-09:15 Precise etching technology of ultra thin Al<sub>2</sub>O<sub>3</sub> film using BCl<sub>3</sub> chemistry

Cheng Tian, Beijing NAURA Microelectronics Equipment Co., Ltd.

09:15-09:30 Reactive Ion Beam Etching of Slanted Gratings for AR Applications

Shuo Dong, Jiangsu Leuven Instruments Co.Ltd.

*09:30-10:00	New development of ICP etching for advanced patterning
	Zhongwei Jiang, Beijing NAURA Microelectronics Equipment Co., Ltd.
10:00-10:15	Coffee Break
Session IV: Per	sists Etch/Wet Etch/Clean/MEMS
Session Chair:	
*10:15-10:45	Review of Advanced Ion Beam Etch Technology: Asymmetrical and Directional Approach
	Yuxin Yang, Jiangsu Leuven Instruments Co., Ltd.
*10:45-11:15	The challenges and new developments on TSV etch applications
	Guorong Li, Beijing NAURA Microelectronics Equipment Co., Ltd.
11:15-11:30	High aspect ratio carbon hardmask etch process for profile and LCDU control
	Mengjiao Zhu, Beijing NAURA Microelectronics Equipment Co., Ltd.
11:30-11:45	Line edge roughness reduction in high aspect ratio carbon hardmask patterning for slit trench
	Li Zeng, Beijing NAURA Microelectronics Equipment Co., Ltd.

Qiao Huang, Jiangsu Leuven Instruments Co., Ltd.

## Session V: BEOL Etching and Memory Etch

**Lunch Break** 

Session Chair: Qingjun Zhao

11:45-12:00

12:00-13:30

*13:30-14:00	Challenges of Inductively Coupled Plasma Applications
	Hu Zhou, Advanced Micro-Fabrication Equipment Inc. China
14:00-14:15	Center to Edge Critical Dimension Uniformity Control in High Aspect Ratio Dielectric Etch
	Jiayu Sun, Lam Research
14:15-14:30	Profile Control for BEOL Tri-layer Patterning Scheme
	Xingxing Xu, Lam Research
14:30-14:45	Coffee Break

A Fully Automated VPD System for Noble Metal Control during CIS manufacturing

## Session VI: ALE and Patterning Session Chair: Kaidong Xu

Session Chair. No	
*14:45-15:15	Plasma etching solutions for compound semiconductors
	Yali Fu, Beijing NAURA Microelectronics Equipment Co., Ltd.
15:15-15:30	Perspective on Plasma Etching in Advanced Packaging
	Yuanwei Lin, Beijing NAURA Microelectronics Equipment Co., Ltd.
15:30-15:45	A Study on Floating Gate Profile Control and Reliability Improvement in Planar 1xnm NAND Flash
	Jun Wang, Peking University
15:45-16:00	Analysis of Key Factors in Reactive Ion Etching of SiC Gate Trench
	Anton Kobelev, Suzhou STR Software Technology Co., Ltd.
16:00-16:15	AlCu Residue Elimination Technique during BEOL Etch Process
	Lian Ye, Jiangsu Leuven Instruments Co.Ltd.
16:15-16:30	Ion Beam Etching as a Solution for Ultra-Precision Planarization Process
	Lei Guo, Jiangsu Leuven Instruments Co., Ltd.
16:30-16:45	Ultra low temperature high aspect ratio OX punch through etching
	Hanlin Cui, Applied Materials

#### Poster Session:

## An optimized approach for High-K first process reliability

Li Fei, Nexchip Semiconductor Corporation

An optimized process for high dielectric metal gate processes to avoid SiGe and NiSi contamination

Yonggiang Ding, HeFei JingHe Semiconductor Corporation

### The LWR improvement in Metal hard mask etch

Songyu Liu, Nexchip Semiconductor Corporation

Metal line width roughness (LWR) improvement by different kind of photoresist (PR)

Chao Ding, Hefei Jinghe Semiconductor Corporation

## **Advanced Patterning LELE Cut LCDU Improvement**

Ting Xie, Advanced Micro-Fabrication Equipment Company Inc.

Sidewall kink elimination of slanted gratings utilizing a twice-etching method

Jiuru Gao, Jiangsu Leuven Instruments Co., Ltd.

## **Residue Improvement in Liner OX Open Process**

Ruxun Yuan, Lam Research

## A STUDY ON THE DIFFERENT APPROACHS OF DUMMY GATE WET REMOVAL APPLICATION

Tianhao Zhang, Lam Research

Mandrel/Non-Mandrel Imbalance Improvement for Self-aligned Reverse Patterning Process

Shiming Zhang, Lam Research

Improvement of Outer Hole Profile Bending in High Aspect Ratio Dielectric Hole Etching

Taojun Zhuang, Lam Research

Improved Si Grass Control during Profile tuning for Silicon Trench Etch in Power MOSFET

Xi Chen, Lam Research

Profile Controlling in High Aspect Ratio Si Trench Etching by Steady-State-Process

Yaming Liu, Lam Research

Research of surface Particle contamination in Selective Nitride Etching Using hot Phosphoric Process

Sutao Liu, Nexchip Semiconductor Corporation

## A study of TiN film queue time effect

Malong Cai, Nexchip Semiconductor Corporation

Ultra-Deep via Etching of Silicon Oxide for High-Voltage Capacitive Isolators

Yuyan Xia, Zhejiang University

Optimization of the Polysilicon Gate Etching Process in SONOS Memory Fabrication

Wanli Yang, Zhejiang University

A Study on Bevel Metal Film Remove for Bevel Peeling Defect Reduction

Liu Xuan, Semiconductor Manufacturing North China (Beijing) Corporation

**Defect Improvement in Process Containing SiOx Passivation** 

JunMing Wang, Lam Research

Sn-Ag Compatible Selective Ti Etch in Cu RDL Fabrication and 3D IC Integration

Chien-Pin HSU, Avantor

## Improvement of Line Roughness of Fin by Conventional Thermal Oxidation and Atomic Level Low-Temperature Ozone Treatments

Peng Wang, Integrated Circuit Advanced Process R&D Center Institute of Microelectronics of the Chinese Academy of Sciences

## The Study of Buffer HF Solution Wet Etch Behavior in Trench Structure

Jiaming Shi, Grandit

## Investigation of the Al Etching Rate Change in Copper Damascene Clean Formulation Chemical

Yipeng Wu, Grandit. tech.Co., Ltd.

## Reaction temperature impact on Siconi® process

Songtao Lv, applied materials

## MTBC Enhancement through new WET Clean implement for preventing wafer breakage

Chunlong Qiu, Applied Materials

## A low-cost solution for Selectra™ Si Chamber Etch rate drift

Jing Cao, Applied Materials

## Reduce AIF Byproduct Caused ESC Backside Helium Leak in Etch Chamber

Longjie Yu, Applied Materials

## Impacts of Al<sub>2</sub>O<sub>3</sub> Window aging on Plasma Ethcing Process

Yanfeng Zhao, Semiconductor Manufacturing International Corporation

## TiN Hard Mask Open Comprehensive Study

Shuda Xu, Applied Materials

## Improvement of CIS TM Profile by Adjusting Gas Ratio

Ziyue Xuan, Applied Materials

## Al BEoL Via Etching Challenge and Solution on Producer-GT™

Sichao Zeng, Applied Materials

## **Producer-GT™ High Productivity CCP Etch Solution**

Xipeng Tong, Applied Materials

## Application of Advanced Pulsing Plasma on DRAM Buried Wordline Fin Profile and Micro Loading Control

Kevin Yao, Lam Research

## Application of Hardware and Process Fine Tune for Chamber Matching in DRAM Critical Etch

Nick Fang, Lam Research

### Buried-Worldline Omega-Shape Profile Control and Impact in DRAM

Liubo Ma, Lam Research

### Mandrel Etch Tuning for Imbalance Improvement in Reverse SADP

Shipeng Gong, Lam Research

#### Inline Critical Dimension Uniformity Improvement in DRAM Capacitor Hard Mask Etch

Wei Wang, Lam Research

## **Bosch Process in TSV Application for Controllable Profile and Uniformity**

Haoran Cao, Lam Research

## Application of Advanced Pulsing and Novel Chemistry in DRAM Capacitor Etch Application

Haoran Cao, Lam Research

## HAR HMO tilting offline monitor and chamber to chamber matching solution

Kai Hu, Applied Materials

### Methods of Profile Control in HVCAP VIA Etching

Tongyao Zhao, Applied Materials

ofile Contro	of CIS	<b>BVia Silicon</b>	Etch
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Le Jiang, Applied Materials

Control of BLC Trench Profile Angel in DRAM BLC Etch

Yuchen Jiang, Lam Research

Advanced Mixed Mode Pulsing in DRAM Active Area Etch

Zheng Ruan, Lam Research

The DRAM Capacitor LCDU Improved by Patterning Optimization

Yuyang Sun, Lam Research

A Study of Al etch process defects

Jiajie Li, Applied Materials

Advanced Pulsing in LELE Application for Controllable Profile

Hui Xu, Lam Research

300mm AL(0.5%Cu+1%Si) Etch Challenge and Solution on Advantage Edge Metal™

Jianjun Liao, Applied Materials

TiN selectivity improvement for All-in-one Etch

Yifeng Xu, Applied Materials

BCD process contact-etch challenges and solutions at Producer GT

Gang Sheng, Applied Materials

Filled Metal height uniformity optimization in BCAT

Lin Luo, Applied Materials

Study of A-Si as Dry Etch Hard Mask in BEOL Low-k Dielectric Patterning

Juxin Yin, Zhejiang University

Si Trench Profile Control in PMOS Silicon Recess Etching

Zhe Li, Lam Research

Study on Integrated Trench Etching for Trench-Type Power MOSFET

Jingru Shen, Zhejiang University

An approach to achieve a flat bottom in Si trench with oxide & poly pillar

Wei Gu, Applied Materials

Approaches of Pitch Walking Improvement in SAQP Patterning

Rishuai Zheng, Applied Materials

A Method of VIA Etch CD Range Improvement

Qunfeng Wen, Applied Materials

Effect of Low Damage Strip on Si and SiGe Surface State

Shijing Wang, Shanghai AnBang Semi Equipment Co., Ltd.

Oxide Remain Control for BCD ONO Spacer Etch on AMAT Producer GT\_Wang Miao\_Etch

Miao Wang, Applied Materials

Sym3 Chamber RF Plasma Stability Improvement

Jie Wang, Applied Materials

Gate oxide removal development for legacy node on SiCoNi

Fan Zhou, Applied Materials

**Excellent Profile Control for Micro-OLED Anode Etch** 

Lijun Shan, Applied Materials

The influence of etching conditions on local loading in Deep Silicon Etching

Yiming Ma, Beijing NAURA Microelectronics Equipment Co., Ltd.

## A STUDY OF DEEP HOLE ETCHING IN MO&DIELECTRIC ALTERNING MULTILAYER STRUCTURE

Zhe Wang, Beijing NAURA Microelectronics Equipment Co., Ltd.

A Study of High Aspect Ratio Si Trench in Cycle Mode Etching with Mask no Loss

Teng Zhang, Beijing NAURA Microelectronics Equipment Co., Ltd.

Side-wall angle uniformity improvement during ICP etch

Dong Li, Beijing NAURA Microelectronics Equipment Co., Ltd.

Two Step Etching Method for Removing Thick Photoresist

Long Ji, Beijing NAURA Microelectronics Equipment Co., Ltd.

Flattening the Silicon Nitride surface of semiconductor chips through etching

Donghan Wang, Beijing NAURA Microelectronics Equipment Co., Ltd.

Reducing Side Cutting During Wet Etching of Gate oxide layer for 28HK metal gate process

Chunshan Zhao, Shanghai Huali Integrated Circuit Corporation

A dry etch method to improve trench type oxide contact etch sidewall striation caused by incoming photo resist roughness

Shanshan (Sera) Nie, Lam Research

A Study on RCA clean particle performance improvement

Xiaowei Cheng, Lam Research

Application of Advanced Plasma Pulsing in a R-SADP (Reversed Self-aligned Double Patterning) Etch Process

Peng Zuo, Lam Research

**Novel Method for Titanium Nitride Wet Etch Thickness Dynamic Control** 

Chen Zhang, Lam Research

Wafer Thinning Thickness Control with In-situ Measurement on Rough Silicon Surface

Zhi Shen, Lam Research

**Nested Bosch Process** 

Changhuo Liu, Semiconductor Manufacturing North China

Optimized AMMP for High Aspect-Ratio Bottom Contact Open Process in DRAM Applications

Rick Yang, Lam Research

## Symposium IV: Thin Film, Plating and Process Integration

Sunday, March 17, 2024 Shanghai International Convention Center

Meeting Room: 5th Floor Yangtze River Hall

Session I: Device Integration - 1 Session Chair: Xiaoping Shi

13:30-13:35 Opening Remarks

*13:35-14:00	Tailoring the deposition and composition of advanced oxide and SiCN films to deliver the highest bonding energy for fusion and hybrid bonding applications  Zongbin Wang, Applied Materials
*14:00-14:25	A Review in III-Nitride Nanocolumns Growth and Applications
	Enrique Calleja, Universidad Politécnica de Madrid
*14:25-14:50	Advances and Reliability Challenges in Heterogeneous Integration in Chiplet Era: from Solder to Copper to Optical Interconnects
	Zhuo-Jie Wu, HFC Semiconductor
14:50-15:10	Optimization of Deep Trench Isolation on 0.18µm SOI BCD Technology for Automotive Application
	Siti Aisah Mohd Salleh, X-FAB Sarawak Sdn. Bhd.

Session II: Device Integration - 2

Session Chair: Chao Zhao

15:10-15:25

\*15:25-15:50 The Progress and Challenges of Large Scale Integration of Silicon Photonics

Adam Lewis, CUMEC

\*15:50-16:15 Do we need 300mm GaN?

**Coffee Break** 

Kai Cheng, Enkris Semiconductor, Inc

\*16:15-16:40 Si based GaN HEMTs/System R&D and the perspective of the technological

commercialization

Hongyu Yu, Southen University of Science & Technology

Monday, March 18, 2024 Shanghai International Convention Center

Meeting Room: 5th Floor Yangtze River Hall

**Coffee Break** 

Session III: ALD Process Development - 1

Session Chair: Jianhua Jv

10:00-10:20

*08:30-08:55	Thin Film Atomic Layer Deposition and Selective Processes
	Rong Chen, Huazhong University of Science and Technology
*08:55-09:20	A Chemistry Perspective of ALD Precursors' Properties
	Xiabing Lou, Origin Deposition Materials Co., Ltd.
09:20-09:40	Characterizing low-k (SiCON) film with different element composition
	Wenxu Duan, Beijing NAURA Microelectronics Equipment Co., Ltd.
09:40-10:00	ALD of Dielectric Materials: Analysis of Equipment Design and Process Performance Using Detailed Modeling
	Yanlin Mao, Suzhou STR Software Technology Co., Ltd.

Session IV: Mem Session Chair: J *10:20-10:45	, 0,
*10:45-11:10	The effect of stress on HfO₂-based ferroelectric thin films
	Feng Luo, Nankai University
*11:10-11:35	SiGe/Si Heteroepitaxial Epitaxy and Characterization for CMOS and Vertically Stacked DRAM
	Guilei Wang, Beijing Superstring Academy of Memory Technology
*11:35-12:00	Modeling of Endurance Degradation of Anti-ferroelectric Hf <sub>1-x</sub> Zr <sub>x</sub> O <sub>2</sub> Capacitor
	Yaru Ding, Zhejiang University
12:00-13:30	Lunch Break
Session V: Device Integration - 3 Session Chair: Chenyu Wang	

Session Chair: Chenyu Wang		
13:30-13:50	The Formation of Air-gaps Isolation Used in Metal/Dielectric Stacking	
13:50-14:10	Weidu Qin, Beijing Superstring Academy of Memory Technology  SMT OPTIMIZATION OF PMOSFET BASED ON MULTI-DEPOSITION AND IN-SITU N2  PLASMA TREATMENT  Longyue Zheng, Zhejiang University	
14:10-14:30	FEA of Thermo-mechanically Induced Crack in IMD	
	Colin Chan, X-FAB Sarawak Sdn. Bhd.	
14:30-14:50	Backside Deposition of LTO/Poly-Si Sealing Layer by One-step PECVD and Post Annealing  Junxian Gao, Lam Research	
14:50-15:10	Copper Diffusion Improvement by Optimizing TaN and Integration in Power Device	
15:10-15:30	Xiangyu Zhou, Beijing NAURA Microelectronics Equipment Co., Ltd.  A machine learning study to obtain an optimal processing pulsed frequency on reactive pulsed DC sputtering of aluminum nitride films  Xue-Li Tseng, National Central University	
15:30-15:45	Coffee Break	

Session VI: Process Development - 1 Session Chair: Xun Gu		
15:45-16:05	Full Wafer Combinatorial Deposition with In-situ XPS/UPS Characterizations	
	Weimin Li, Shanghai Institute of IC Materials Co., Ltd.	
16:05-16:25	Tungsten Surface Roughness Improvement by Single Deposition Process	
	Zhengning Gao, Lam Research	
16:25-16:45	The Effects of Different Silicon Oxide Substrates on Amorphous Silicon Thin-Film	
	Zhengdao Liu, Beijing NAURA Microelectronics Equipment Co., Ltd.	
16:45-17:05	A Novel Thin Film Deposition Method by IBD for Asymmetrical Patterns	
	Zichao Li, Leuven Instruments	
17:05-17:25	Potential confusion in the analysis of the current-voltage characteristics of high-k dielectric on lightly doped p-type silicon MIS capacitors Wai Shing Lau, Nanyang Technological University	

## 17:25-17:45 The secret of the leakage current mechanism in some historical device-quality high-k metal-insulator-metal capacitors

Wai Shing Lau, Nanyang Technological University

#### Poster Session:

## Optimizing Si/SiO₂ Interface of Planar LDMOS Field-Effect Transistors for Medium-Voltage Power Applications

Jiaoyang Chen, Huahong Semiconductor (Wuxi) Limited

Study of HDPCVD Charge Improvement for ILD Process

Jie Yang, Lam Researchc

## IMPROVED PERFORMANCE OF PMOS BY OPTIMIZING THE EPITAXIAL MORPHOLOGY

Tao Wang, Shanghai Huali Integrated Circuit Corporation

Exploring the Effect of Gate Oxide Process on the Electrical Performance of the CMOS Device

Yongkang Hu, University of Science and Technology of China

## Improving Gate Oxide Uniformity Using Wet-Dry Oxidation

Lin Tang, School of Micro-Nano Electronics, Zhejiang University

### **NiSix Anneal on Producer Pyra**

Heping Du, Applied Materials

## DRAM Bit line Evaluation by using Single Precursor Activate Radical Chemistry (SPARC) Process

Guanfeng Lu, Lam Research

## W CVD Process Extendibility Development for Challenging Gap Fill

Shao Rui, Applied Materials

## **NBTI Improvement Through Gate Process Optimization**

Ying Ma, Applied Material China

### **Excellent Performance of PC XT in Soft-Clean**

Xingluan Long, Applied Materials

#### Amorphous Silicon Bump Defect Mechanism Analysis and Improvement Strategy

Shudi Min, Applied Materials

#### Approach of Customized Thickness Profile and Superior Uniformity on SACVD

Xiang Li, Applied Materials

### HARP STI Wafer Sliding and Pre-heat Improvement by Recipe Optimization

Yiyu Zhang, Applied Materials

#### HARP STI Range Improvement for 28nm HKMG Double Patterning Process

Zhaojie Sun, Applied Materials

#### High Bow wafer Handling Approach on Producer PECVD

Bin Wang, Applied Materials

### Low Dep Rate Oxide Process Development for Glue Layer

Congcong Zhao, Applied materials

### **Excellent Stability Control for High Throughput DARC Process**

Chao Zheng, Applied Materials

### N-Dosage Non-Uniformity Tuning in Nitride Incorporated Gate Oxide Process

Eira Yang, Applied Materials

#### High Productivity of Advanced Al PVD in Al Slab

Xiaogang Su, Applied Materials

## SiGe Epitaxy Improved by Si Cap Technology

Tao Wang, Shanghai Huali Integrated Circuit Corporation

Effect of process parameters on microstructure and properties of ITO films by pulsed magnetron sputtering

Yanmeng Chen, Beijing NAURA Microelectronics Equipment Co., Ltd.

The Influence of Different Parameters on Capacitive Coupled Magnetron Sputtering Process

Song Yang, Beijing NAURA Microelectronics Equipment Co., Ltd.

Effect of process gas pipline on TiN film resistance

Hongwei Geng, Beijing NAURA Microelectronics Equipment Co., Ltd.

**TiN Infilm Particle Improvement by Bias Field Integration** 

Xin Wang, Beijing NAURA Microelectronics Equipment Co., Ltd.

Tool transfer compatibility improvement for different thin wafer type

Jiaxi Liu, Applied Materials

## Symposium V: CMP and Post CMP Cleaning

Sunday, March 17, 2024 Shanghai International Convention Center

Meeting Room: 5D+5E

Session I: prensent and future Session Chair: Xinping Qu

\*\*13:30-14:00 CMP equipments and application technologies for advanced manuafacturing process

Xinchun Lu, Tsinghua University

\*14:00-14:25 CMP Technology for More than Moore Innovation

Haedo Jeong, Pusan National University

\*14:25-14:50 New methodology for anisotropic nanoparticles characterization by polarization light

scattering: length and diameter determination of rod-like nanoparticles

David Jacob, Cordouan Technology

14:50-15:10 Coffee Break

Session II: ILD and STI slurry Session Chair: Shoutian Li

\*15:10-15:35 Ceria slurry applications to STI, ILD and advanced packaging CMP

Yuchun Wang, Anii microelectronics

\*15:35-16:00 From Good to Great: The Power of Advanced ILD CMP Slurries in Boosting Performance

Juliane Hitzel, Advanced NanoSurface Technologies Co., Ltd.

16:00-16:15 CeO<sub>2</sub> slurry post rinse condition research in STI CMP technology

Zhengyi Li, Semiconductor Manufacturing North China (Beijing) Corp.

16:15-16:30 INCOMING IMPACT ON DISHING IMPROVEMENT IN FEOL PROCESS

Huize Du, Shanghai Huali Integrated Circuit Corporation, Shanghai, China

16:30-16:45 Positively charged ceria particles cleaning by HCOOH-H<sub>2</sub>O<sub>2</sub>-DIW solution

Wenlong Tang, Fudan University

16:45-17:00 Study on the dispersing effect and mechanism of LABSA on SiO₂ in an alkaline barrier

slurry

Fangyuan Wang, Hebei University of Technology

Monday, March 18, 2024 Shanghai International Convention Center

Meeting Room: 5D+5E

Session III: Metal CMP

**Session Chair: Jingxun Fang** 

\*09:00-09:25 Mechanism Research and Improvement of AL Scratch Defect Based on MG CMP

Qingqing Duan, Shanghai Huali Integrated Circuit Corp.

09:25-09:40 Cu post CMP cleaner development utilizing Al system

Atsushi Mizutani, Fujifilm corporation

09:40-09:55 Effect of Green Corrosion Inhibitors on the Performance of Copper-Cobalt CMP

Chao He, Institute of Microelectronics, Hebei University of Technology

09:55-10:10 Effect of Green Additive Sarcosine as Inhibitor for Cobalt-Based Copper Interconnect

CMP

ChangXin Dong, Hebei University of Technology

10:10-10:30 Coffee Break

**Session IV: Compound Semiconductor CMP** 

Session Chair: Baoguo Zhang

\*10:30-10:55 The development progress of new high-efficiency silicon carbide substrate polishing

slurry

Xiuyan Sun, Zhangjiagang Anchu Technology Ltd.

\*10:55-11:20 Research on the electro-fenton magnetorheological finishing technology for GAN wafer

Qiusheng Yan, Guangdong University of Technology

11:20-11:35 Study on the Slurry for Chemical Mechanical Polishing of GaN Wafer

Steve Liu, Hebei University of Technology

11:35-13:30 Lunch Break

Session V: Novel Films CMP and Process

Session Chair: Jie Chen

\*13:30-13:55 CMP characteristics of IGZO thin film with a variety of process parameters

Ming Zeng, Beijing Superstring Academy of Memory Technology, Beijing, China

\*13:55-14:20 Study on the Processing Characteristics and Polishing Technology of Easily Cleavable

**Gallium Oxide Crystals** 

Hai Zhou, Yancheng Institute of Technology

14:20-14:35 Chemical Effect Mechanism in Chemical Mechanical Polishing of Silicon Wafer

Chenwei Wang, Jiangsu Shanshui Semiconductor Technology Co., Ltd.

14:35-14:50 EOE evolution processes of same step profile in CMP with different one-material

polishing time

LIXiao Wu, Lanzhou University of Technology

14:50-15:05 Effect of Surfactants on CMP Properties of C-, A- and R-plane Sapphire

Xinjie Li, Hebei University of Technology

15:05-15:25 Coffee Break

#### **Poster Session:**

A Novel Endpoint System Application On DRAM W CMP Application

Lin Wang, Applied Materials

DISHING STUDY ON CHEMICAL MECHANICAL PLANARIZATION (CMP)

Huize Du, Shanghai Huali Integrated Circuit Corporation, Shanghai, China

ILD-CMP Wafer Edge Thickness Profile Stability Improvement Via Acid Silicon Oxide Slurry Formulation Design

Zhijie Zhang Liang Tian, Semiconductor Manufacturing North China (Beijing) Corp, Beijing, China

Study on Ceria Slurry for Chemical Mechanical Polishing of 4H-SiC

Sihui Qin, Hebei University of Technology

The effect of CeO<sub>2</sub> / SiO<sub>2</sub> composite abrasive on the performance of silicon CMP under low concentration conditions

Liu Wenbo, Hebei University of Technology

Chemical Mechanical Planarization of SiC Si-face by Al2O3-based acid slurry

Zehao Yue, Hebei University of Technology

Multiple approaches to achieve high throughput of Cu CMP process in LK 3 platens platform

Jiaming Xu, Applied Materials

Achieved World-Class BSI Si CMP TTV Performance via FVXE NIR® MPC System

Likun Cheng, Applied Materials

## Study on chemical-mechanical synergies in polishing of ruthenium

Hongyu Di, Dalian University of Technology

**Effects of Polyvinyl Alcohol on Silicon Chemical Mechanical** 

Shuangshuang Lei, Hebei University of Technology

Motor torque algorithm and polish pressure optimization in STI CMP Process

Chen Qiang, Applied Materials

RTPC XE for 28nm BEOL Cu CMP

Youlai Xiang, Applied Materials (China), Inc. China

Study on 28nm Technology Node ILD0-CMP Micro\_Scratch Defect Reduction

Xing Ma, Shanghai Huali Integrated Circuit Corp.

China 1st RTPC X/Fullscan X implemented in LK Metal CMP

Zhenxing Song, Applied Materials (China)

Feasibility Analysis of Skip ILD-CMP Scheme on 28nm Technology Node

Fan Chen, Shanghai Huali Integrated Circuit Corp.

A Trade-off Balance Between Cu Corrosion and Cu Oxide Defect

Chenyu Zhou, Shanghai Huali Integrated Circuit Corp.

The Precise Profile Control of RTPC X in CIS Cu CMP

Mengxia Li, Applied Materials

**Micro-Scratch Defect Improvement for CMP Process** 

Kun Zhang, Applied Material

## Symposium VI: Metrology, Reliability and Testing

Sunday, March 17, 2024 Shanghai International Convention Center

Meeting Room: 3B

Session I: Test I

Session Chair: Xiaowei Li

12.20-12.25 Opening Remarks

13:30-13:35	Opening Remarks
*13:35-14:00	Jitter reduction for multi-GHz ATE up to 20 GHz
	Dave Keezer, Eastern Institute for Advanced Study (EIAS) in Ningbo, China.
*14:00-14:25	Assessing the Power-Awareness of VLSI Testing
	Xiaoqing Wen, Kyushu Institute of Technology, Japan
14:25-14:40	An Efficient Library for Protocol Test on V93000
	Peifeng Ni, Advantest (China) Co., Ltd.
14:40-14:55	Address the challenges of mass production testing for 5G millimeter devices
	Daniel Sun, Advantest (China) Co., Ltd.
14:55-15:10	Highly multi-sites front end test solution design and implementation for automotive testing
	Kaitao Liu, Advantest (China) Co., Ltd.
15:10-15:25	Mirroring ATPG Technology for Multi-Core Chips
	Jitong Zhou, Sanechips Technology
15:25-15:40	Deep Reinforcement Learning-Based Automatic Test Pattern Generation
	Wenxing Li, Institute of Computing Technology, Chinese Academy of Sciences
15:40-15:55	Coffee Break

Session II: Metrology I

**Session Chair:** 

\*15:55-16:20 Doping level detection in Si or SiGe via In-Line Raman Spectroscopy

Ilya Osherov, Nova Ltd.

16:20-16:35 Investigation on the root cause of ESD failure of large size WBBGA package chip

Yunhe Zhang, Sanechips Technology Co., Ltd.

The Influence of Pin Position on CDM Peak Current of Chips Based on Large-Sized 16:35-16:50

**CoWos Package** 

Liyi He, Sanechips Technology Co., Ltd.

16:50-17:05 Depth-profile Analysis of AlAsGa film via Grazing Incident X-ray fluorescence

Xujun Li, Shenzhen Angstrom Excellence Semiconductor Technology Co., Ltd.

Monday, March 18, 2024 Shanghai International Convention Center

Meeting Room: 3B

Session III: Test II **Session Chair:** 

\*08:30-08:55 Polymorphic Circuits Design and Applications in Security

Gang Qu, University of Maryland, USA

Breakthrough the test challenges for the latest Beidou navigation and satellite 08:55-09:10

communications chips

Xi Liu, Advantest (China) Co., Ltd.

09:10-09:25	Advanced Digital Baseband Signal Generation and Processing Solution for V93000 5G Small Cell Transceiver Testing
	Bank Liu, Advantest (China) Co., Ltd.
09:25-09:40	Various Driver test Summary on V93000 in Automotive Device
	Yang Lin, Advantest (China) Co., Ltd.
09:40-09:55	A new fast XRD apparatus for the epitaxial films with a focusing X-ray Beam
	Yankun Sun, Shenzhen Angstrom Excellence Semiconductor Technology Co., Ltd.
09:55-10:10	An Efficient Protocol ATE Solution for Driver IC on Advantest T6391
	Xiang Cai, Advantest (China) Co., Ltd.

## Session IV: Metrology II

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Session Chair:	
*10:10-10:35	MI's solutions for next era
	Byoung-Ho Lee, Hitachi High-Tech Corporation
10:35-10:50	Metryx solution for dishing defect in Ultra thick metal ECP process
	Joey Hu, Lam Research
10:50-11:05	Assessing Brittleness of Substrates and Thin Layers with Nanoindentation
	Zhiming Zhang, KLA Instruments Group
11:05-11:20	Advantages of Picosecond Laser Acoustics to Process Control of Semiconductor Power Devices
	Johnny Dai, Onto Innovation
11:20-11:35	Multi-physics Simulation of Electromigration in Cu Interconnect
	Xuefeng Zhang, Beijing NAURA Microelectronics Equipment Co., Ltd.
11:35-11:50	Analysis and Protection Solution for Aging DC-stress Induced Waveform Distortion Issues
	Haiyong Wang, Sanechips Technology Co., Ltd.
11:50-12:05	Modern X/Y metrology system addressable to mature semiconductor nodes
	Xueying Hai, Mycronic AB
12:05-13:30	Lunch Break

## Session V: Reliability

Signal and Power Reliability for Integrated Chips and Chiplets
Lei He, UCLA, USA
Electro Optical Time Domain Reflectometry for Advanced Package Failure Analysis
Longhai Liu, Advantest (China) Co., Ltd.
Test solution to prevent Dynamic Voltage Stress burning issue on ATE
Haijing Wu, Advantest (China) Co., Ltd.
Reliability challenges in SiC components – performing dynamic test methodologies like
DGS for meaningful measurement results Sandro Strasser, SET GmbH, NI
Study on Failure Mechanism of C4 Bump Solder Excursion in CoWoS Package
Xixiong Wei, Sanechips Technology CO., Ltd.
Coffee Break

Session VI: Test Session Chair:	
*15:10-15:35	Scaling of Memory Performance and Capacity with Memory Processor
	Fei Wang, Shandong University
15:35-15:50	Novel Process Control Solutions for Advanced Power and Automotive Semiconductor Devices
	Terry Chen, Applied Materials
15:50-16:05	A Dynamic Reusable Structure of I/O Pads for Scan Chains
	Qi Cheng, Sanechips Technology
16:05-16:20	V93000 test solutions introduction for Audio PA device
	Junlin Wang, Advantest (China) Co., Ltd.
16:20-16:35	A Closed-loop Chip Fast Binning Technology

#### Poster Session:

Test solution of mini-LVDS interface transmitter for media chip on V93000 platform Ying He, Advantest (China) Co., Ltd.

Testing implementation and challenges of processor with power path switching feature Liuhao Chen, Advantest (China) Co., Ltd.

A fast measurement scheme for high-speed loopback pin continuity testing

Liuhao Chen, Advantest (China) Co., Ltd.

Jiawei Wang, Sanechips Technology

A New Flexible Binning Method in ATE Production

Hanru Zhang, Advantest (China) Co., Ltd.

A Universal DPAT GUI Solution for Production Test

Hao Chen, Advantest (China) Co., Ltd.

Picosecond Ultrasonics Applications on Electroplated Cu Process

HuaYuan Li, Onto Innovation

A Robust Calibration Test Solution for High-Performance Computing SoC Tsensors Yang Zhang, Advantest (China) Co., Ltd.

A common framework solution for firmware test on V93000 ATE platform

Yanyan Chang, Advantest (China) Co., Ltd.

Study of Coating Effect on TEM Sample Damage and Elemental Analysis Yun Xu, SMIC

A Universal Auto Configured Efuse Solution on ADVANTEST V93000 ATE Platform Yefang Wang, Advantest (China) Co., Ltd.

Optimized Filling Capacity in HARP Process for STI void Defect Improvement in 28nm Technology

Zhimin Zhang, Shanghai Huali Integrated Circuit Corporation

Influence of Foup Environment On Defects in Semiconductor manufacturing

Weiwei Zhao, Shanghai Huali Integrated Circuit Corporation

Streamlining Chip Testing with Simplified Digital Data Acquisition

Felix Chen, Advantest (China) Co., Ltd.

Comparison of simulation and test results of multi-type ring oscillators on advanced process nodes

Kuili Chen, Sanechips Technology

## Optimization and Validation of Sampling and TD-GCMS Analysis for Volatile Organic Compounds from Semiconductor Cleaning Coupons

Ling Wang, Ferrotec Technology Development (Shanghai) Co., Ltd.

Application of Pulse Id-Vg Technique on 55nm Low Power Platform

Gang WANG, Hangzhou HFC Semiconductor Corporation

New Generation Test Framework Solution for Complicated Multi-Die Chip on ATE

Kai Zhou, Alibaba-Thead

Virtual Measurement Combine OCD and FDC through Optimized Random Forest Machine Learning Algorithm Assists on Post Etching Monitor

Qingyun Yang, SiEn (Qingdao) Integrated Circuits Co., Ltd.

Characterization of Ultrathin Films in HKMG by Spectroscopic Ellipsometer

Yufan Zhang, Shenzhen Angstrom Excellence Semiconductor Technology Co., Ltd.

Study on STEM EDS for GeSi Atomic Layer Interface Identified and Concentration Quantified

Fan Zhang, SMIC

An optimized ADC&DAC test solution from SmartScale MCx to ExaScale WSMX

Tianyu Zhang, Advantest (China) Co., Ltd.

**Spectra Machine Learning for the Prediction of Sheet Resistance and Capacity** 

Shang Li, SiEn (Qingdao) Integrated Circuits Co., Ltd.

Quantitative analysis of the damage degree of the single-crystal silicon induced by ion implantation using an optical approach

Emma Wu, SiEn (Qingdao) Semiconductor corporation Co., Ltd.

Detecting the B concentration in the SiGeB epilayers utilizing a hybrid approach combining HR-XRD and XPS

Emma Wu, SiEn (Qingdao) Semiconductor corporation Co., Ltd.

A new multi-mode X-ray fluorescence apparatus for both blanket and pattern wafer film metrology

Yuxiang Huang, Shenzhen Angstrom Excellence Technology Co., Ltd.

The Influence of Metal Barrier Punch Through Process on Dielectric Reliability at 55nm CMOS node

Chenxiao Xu, Zhejiang University

Tunability Demonstration of RadiancePlus® on Spike Anneal Process

Xiaolong Wang, Applied Materials

Sample Preparation Method for In-Situ Tem Analysis in Integrated Circuits

Guoyang Ye, Semiconductor Manufacturing International (Shanghai) Corporation Failure Analysis Laboratory

## Symposium VII: Packaging and Assembly

Sunday, March 17, 2024 Shanghai International Convention Center

Meeting Room: 5B+5C

Session I: 3D and Advanced Packaging Technologies

Session Chair: Steve X. Liang 13:30-13:35 Opening Remarks

\*13:35-14:00 Chiplets and Advanced Packaging for Future Computing

Terry Wu, Samsung Electronics

14:00-14:20 Challenges of Semiconductor Micro Via Fabrication Technology for 3D Chiplet

Interconnect

Yasuhiro Morikawa, ULVAC, Inc.

14:20-14:40 Comprehensive Investigation of Insufficient IMC in SOIC Through Advanced Statistical

**Analysis** 

Jingwei Sun, NXP Semiconductors

\*\*14:40-15:10 Heterogeneous Integration Ecosystem: The Critical Path to the Success of 3D SOC(SOH)

Eason Wang, ICLeague

15:10-15:30 Coffee Break

**Session II: Novel Packaging Materials and Process** 

**Session Chair:** 

15:30-15:50 Hybrid Wafer-to-Wafer and Die-to-Wafer Technology for Heterogenous Integration

**Applications** 

Viorel Dragoi, EV Group

15:50-16:10 Glass As An Enabling Material for Advanced Packaging

Jay Zhang, Corning Incorporated

Monday, March 18, 2024 Shanghai International Convention Center

Meeting Room: 5B+5C

Session III: Inspection, Test and Reliability

Session Chair: X. Wu

\*09:00-09:25 Study on ELK Dielectric Reliability During the Solder Reflow Process Based on Finite

**Element Simulations** 

Jialin Zheng, Sanechips Technology Co., Ltd.

09:25-09:45 A Modularized Thermal Test Chip Design and Verification

Jianjun Sun, Sanechips Technology Co., Ltd.

09:45-10:05 Evaluating 224G SI Performance of Vertical Interconnections on Package Substrate and

PCB

Kai Yuan, Sanechips Technology Co., Ltd.

10:05-10:20 Coffee Break

Session IV

Session Chair: M. Huang

10:20-10:40 Heat Transfer Improvement of Phase Change Material with Metal Foam

Yan Zhang, Shanghai University

*10:40-11:05	Study of Defects in Advanced Packing at the Atomistic Scale by Using In Situ TEM
	Xing Wu, East China Normal University
*11:05-11:30	The Solution and Challenge of Glass Core Substrate Technology
	Tingyu Lin, Guangdong FoZhiXin (FZX) Microelectronics Technology Research Co., Ltd.
*11:30-11:55	Breaking Memory Wall with SeDRAM® Technology in Chip Level
	Fengguo Zuo, Xi'an UniIC Semiconductors Co., Ltd.

### **Poster Session:**

Thermal and Thermal Stress Simulation Analysis of Embedded Microchannel Cooling on Large-Size Packaging

Fusheng Meng, Sanechips Technology Co., Ltd.

Improvement of Warping Simulation Accuracy and Influence Factors Analysis in FCBGA Package

Yubo Wang, Sanechips Technology Co., Ltd.

## Symposium VIII: MEMS, Sensors and Emerging Semiconductor Technologies

Sunday, March 17, 2024 Shanghai International Convention Center

**Meeting Room: 5A** 

Session I: Emerging materials and devices

Session Chair: Jianshi Tang, Tsinghua University

13:30-13:35 **Opening Remarks** Advancing 3D Nano-electronic Systems through Innovations in BEOL-Compatible Oxide \*13:35-14:05 **Semiconductor Technology** Gong Xiao, National University of Singapore, Singapore \*14:05-14:35 **XOI** materials Xin Ou, Shanghai Institute of Microsystem and Information Technology, China Si based GeSn materials and devices \*14:35-15:05 Chuanbo Li, Minzu University of China, China 15:05-15:20 Coffee Break \*15:20-15:50 Antimonide semiconductor material for infrared sensing Donghai Wu, Institute of Semiconductors, China Lamb Acoustic Wave Device for RF applications: Ready for Prime Time Challenges and

Monday, March 18, 2024 Shanghai International Convention Center

Songbin Gong, Spectron Tech, C4hina/UIUC, USA

**Meeting Room: 5A** 

11:40-13:30

\*15:50-16:20

**Session II: 2D materials** 

Session Chair: Wei Wang, Peking University

**Lunch Break** 

Applications?

08:30-08:35	Opening Remarks
*08:35-09:05	Controllable preparation of wafer-scale two-dimensional van der Waals heterostructures Libo Gao, Nanjing University, China
*09:05-09:35	Atomically sharp interface of van der Waals heterostructures enabled high-performance electronic devices
	Lihong Bao, Institute of Physics, Chinese Academy of Sciences
*09:35-10:05	NEMS based on novel vdW heterostrucutres
	Zheng Han, Shanxi University, China
10:05-10:20	Coffee Break
*10:20-10:50	High-mobility 2D P-type semiconductor materials
	Xiang Chen, Nanjing University of Science & Technology, China
*10:50-11:20	Universal Materials and Device Integration Technology for Future Chips
	Chen Wang, Tsinghua University, China
11:20-11:40	A Graphene Field Effect Transistor (GFET) based Integrated Biosensor System For Point-Of-Care Application
	Ziyang Zhu, Fudan University, China

Session III: MEMS & Sensors Session Chair: Chen Wang, Tsinghua University 13:30-13:35 **Opening Remarks** \*13:35-14:05 A GHz Silicon-based Width Extensional Mode MEMS Resonator with high Q Jinling Yang, Institute of Semiconductors, Chinese Academy of Sciences \*14:05-14:35 **MEMS Acoustic Device** Songsong Zhang, Chengdu Xiansheng Technology/SITRI, China \*14:35-15:05 Advanced spectral sensing methods for process monitoring applications Ray Saupe, Fraunhofer ENAS, Germany **Coffee Break** 15:05-15:30 TSV INTEGRATED and Pattern Recognition based Multimode Degenerated Low-power 3-15:30-15:50 dimensional Smart sensing chips Simian Zhang, Tsinghua University, China 15:50-16:10 SPAD-based line sensor IC for chemiluminescence assays in microfluidic channels Alexander Zimmer, X-FAB Global Services GmbH, Germany 16:10-16:30 Newly developed low-reflectivity black resist with high optical density Hiroaki Idei, FUJIFILM Corporation, Japan UV-C Light Detection with High Performance Photodiodes Integrated in a 0.18 µm Modular

#### Poster Session:

16:30-16:50

Design and experiment of a micro planar linear motor equipped with electromagnetic quide

Chao Zhi, Shenzhen Technology University, China

Daniel Gäbler, X-FAB Global Services GmbH, Germany

The performance enhancement of CMOS microbolometer with metal-insulator-metalbased plasmonic metamaterial absorbers

Jie Liu, Nanjing University, China

**CMOS Foundry Technology** 

Performance-enhanced CMOS polysilicon microbolometer with narrow supporting arms Wenbin Zhou, Nanjing University, China

Design of arbitrarily polarized CMOS terahertz detector based on plasmonic antenna

Ke Wang, Nanjing University, China Investigation of electrical characteristics of a fabricated IGAD detectors at high and low temperatures

Yupeng Lu, Institute of Microelectronics, China

Research on stereo tactile simulation based on microelectrical osmotic pump technology

Li Zheng, Hefei Visionox Technology Co., Ltd, Kunshan Branch, China

An Intelligent General-Purpose Circuit and System for Broad Sensor Array-Based **Applications** 

Junye Li, Shenzhen University, China

Colloidal quantum dot enhanced short-wavelength infrared absorption of avalanche photodetectors

Lilei Hu, Shanghai University, China

A novel multiple guard ring design for low dark current of backscattered electron detectors

Lilei Hu, Shanghai University, China

A Thin Film Cantilever-Based Magnetoelectric Magnetic Field Sensor and Energy **Harvester Utilizing the Delta-E Effect** 

Yuxi Wang, ShanghaiTech University, China

## Symposium IX: Design and Automation of Circuits and Systems

Sunday, March 17, 2024Shanghai International Convention Center

Meeting Room: 3E

Session I: Keynote Session I

Session Chair: Weikang Qian, Shanghai Jiao Tong University

**13:30-13:35** Opening Remarks

Weikang Qian, Shanghai Jiao Tong University

\*\*13:35-14:05 Scale-out Chiplet-based Systems: Architecture, Design and Pathfinding

Puneet Gupta, University of California, Los Angeles(UCLA)

\*\*14:05-14:35 Photonic-Electronic Design Automation

Jiang Xu, Hongkong University of Science and Technology

14:35-14:50 Coffee Break

**Session II: Design Technology Co-Optimization** 

Session Chair: Yu-Guang Chen, National Central University

\*14:50-15:15 Diffusive/Quantum Carrier Transport and Multiphysics Simulation Methods of Advanced

Electronic/Optoelectronic Devices
Wenchao Chen, Zhejiang University

\*15:15-15:40 Design Technology Co-Optimization Methods for Advanced Logic Nodes

Xingsheng Wang, Huazhong University of Science and Technology

\*15:40-16:05 Machine Learning for Device Modeling (MLDM) in the DTCO Eco-system

Lining Zhang, Peking University

\*16:05-16:30 Exploring Al-in-the-Loop For Physical Design Verification DFM/DTCO EDA

Yongfu Li, Shanghai Jiao Tong University

Monday, March 18, 2024 Shanghai International Convention Center

Meeting Room: 3E

Session III: Keynote Session II

Session Chair: Xunzhao Yin, Zhejiang University

\*\*8:30-9:00 Ultra-broadband RF Front-end SoC using 0.18um CMOS technology

Jianguo Ma, Zhejiang Lab

\*\*9:00-9:30

Session IV: Hardware Security

Session Chair: Xunzhao Yin, Zhejiang University

\*9:30-9:55 Logic Locking over TFHE for Securing User Data and Algorithms

Masanori Hashimoto, Kyoto University

9:55-10:10 A Customized Model for Defensing Against Adversarial Attacks

Jiang Sun, ShanghaiTech University

10:10-10:25 Coffee Break

Session V: EDA		
Session Chair: Pingqiang Zhou, ShanghaiTech University		
*10:25-10:50	Logic Synthesis based on Semi-tensor Product of Matrices	
	Zhufei Chu, Ningbo University	
10:50-11:05	Logic Synthesis for XOR-AND Graphs via Reed-Muller Representations	
	Zhufei Chu, Ningbo University	
11:05-11:20	Integration of Shift Left Updates into Logic Synthesis and Macro Placement	
	Xinfei Guo, Shanghai Jiao Tong University	
11:20-11:35	TimingDTH: Timing-driven placement with Deep Three-Head reinforcement learning	
	Shuai Yuan, Shanghai Jiao Tong University	
11:35-11:50	Decoupling Capacitor Optimization for 2.5D-ICs with Deep Reinforcement Learning	
	Technique	
	Haiyang Feng, Zhejiang University	

**Session VI: AI Accelertors** 

11:50-13:30

Session Chair: A	n Zou, Shanghai Jiao Tong University
*13:30-13:55	Optimizing Architecture and Algorithm for Privacy-Preserving Machine Learning

Jongeun Lee, Ulsan National Institute of Science and Technology

*13:55-14:20	Efficient and Robust Hardware for Neural Networks
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Li Zhang, Technical University of Darmstadt

\*14:20-14:45 Algorithm and Hardware Codesign for Brain-inspired Neuromorphic Computing

Aili Wang, Zhejiang University

14:45-15:00 A Hardware Accelerator for Sparse Computing Based on NVDLA

Yizhou Chen, Zhejiang University

15:00-15:15 Integer Arithmetic-Based and Activation-Aware GELU Optimization for Vision Transformer

Zihan Zou, Southeast University

15:15-15:30 Coffee Break

Session VII: Advanced Circuit and System Design Session Chair: Aili Wang, Zhejiang University

**Lunch Break** 

\*15:30-15:55 A Journey of High-Density Associative Memories based on Ferroelectric Content

**Addressable Memories** 

Xunzhao Yin, Zhejiang University

\*15:55-16:20 Navigating Aging Effects: Concepts and Implementation in Reliable Computing Systems

Yu-Guang Chen, National Central University

16:20-16:35 Enhance the Real-Time Performance of FPGA through Partial Dynamic Reconfiguration

An Zou, Shanghai Jiao Tong University

16:35-16:50 A 16-bit 8MSPS SAR ADC with Configurable Low-Power Comparator

Yidan Liang, Zhejiang University

#### **Poster Session:**

Data Flow Graph Partitioning Method for CGRA Temporal Mapping Based on Bayesian Optimization

Yihan Hu, Fudan University

Verification of 400GbE with Optical Modules on an FPGA Platform

C.-Z. CHEN, Peng Cheng Laboratory

## A transient enhanced output capacitor-less LDO with adaptive biasing and spike reduction

Qianxi Cheng, Peking University

Design of large-scale power battery safety monitoring system

Zixiang Yan, Hangzhou Dianzi University

### **DESIGN OF A 10BITS 100MSPS SAR ADC**

Chaorun Li, Peking University

Runtime Configurable Approximate Computing System for Simulated Annealing Algorithm

Shi Jian, Shanghai Jiao Tong University

An 18.3~42.1GHz octave frequency tuning class-C quadcore VCO achieving 204.5 dBc/Hz FOMT

Shan Lu, Institute of microelectronics of the Chinese Academy of Sciences

Effective Resistance Estimation for Large Circuits Using Random Walk Algorithm Jinyu Zhang, Empyrean Technology Co., Ltd.

A Novel Smart Sampling Approach with Broader Compatibility in Semiconductor Manufacturing

Tianyue Lai, Fujian Jinhua Integrated Circuit Co. Ltd.

Designing and Accelerating Spiking Neural Network based on High-level Synthesis

Heng Zi, Beijing University of Posts and Telecommunications

STOCHASTIC COMPUTING HARDWARE DESIGN AND OPTIMIZATION FOR CONVOLUTIONAL NEURAL NETWORKS

Zhinan Chen, Fudan University

A 106TOPS/W SRAM Compute-In-Memory Macro in 28nm with Reconfigurable Bitwise Operation for Al

Yiqi Meng, Zhejiang University

Application of Community Detection based Parallel MOEA/D Algorithm in RF Power Amplifier Circuit Design

Jiejin Zhou, Fudan University

A Hardware Accelerator of the Convolutional Spike Neural Network Based on STDP Online Learning

Qinxin Chen, Zhejiang University

## Symposium X: AI & IC Manufacturing

Sunday, March 17, 2024 Shanghai International Convention Center

Meeting Room: 5F

Session I: Modeling & Simulation in Intelligent Systems

Session Chair: Yunlong Li

\*\*13:30-13:55

Neuromorphic Audio Edge Intelligence

Shih-Chii Liu, Institute of Neuroinformatics, University of Zurich and ETH Zurich

In-memory Computing and Dynamic Vision Sensors: Recipes for tinyML in Internet of Video Things

Arindam Basu, Hongkong City University

A Novel DES Encryption Circuit Based on RRAM XOR Gates

14:35-14:50 A physical based 2D Monte Carlo Model of MO-ECRAM Programming for Device

Optimization

Haotong Zhu, Peking University

Haoxiong Bi, Zhejiang University

14:50-15:05 Coffee Break

Session II: Future of Manufacturing: Industrial Insights

Session Chair: Yang Xu

\*15:05-15:30 Al Empowers Semiconductor Yield Signoff Ecosystem - Reducing Cost and Increasing

**Efficiency for Manufacturing with a Diversified Supply Chain** 

Mark Lu, Semitronix Corporation

\*15:30-15:55 The Application of Virtual Manufacturing in IC Process Development

Yunlong Li, Zhejiang University

\*15:55-16:20 Depth-first convolution-neural-network pipeline for compute-in-memory architecture

Cimang Lu, Flash Billion

\*16:20-16:45 Progress of Al for EDA Algorithms

Yu Han, Empyrean Technology Co., Ltd.

Monday, March 18, 2024Shanghai International Convention Center

Meeting Room: 5F

Session III: Exploring Non-von Neumann Architectures

**Session Chair: Jinfeng Kang** 

\*\*8:30-8:55 Novel Data Storage Technology for Al

Xiangshui Miao, Huazhong University of Science and Technology

\*8:55-9:20 Developing a Neuromorphic Computer: Practices and Challenges

Gang Pan, Zhejiang University

\*9:20-9:45 Heterogeneous integration of analog and digital computing-in-memory technologies

Shaodi Wang, WITMEM Co., Ltd.

9:45-10:10 The Integration of AI Large Model & Neuromorphic Computing in Memory with High

**Speed Analog Ics** 

Hongjie Liu, Shenzhen Reexen Technology Co., Ltd.

10:10-10:25 Coffee Break

Session IV: Co-o	optimization from Technology, Device to Design
Session Chair: C	Cheng Zhuo
*10:25-10:50	Nonvolatile emerging memory devices for energy-efficient edge Al accelerators
	Daniele Ielmini, Politecnico Di Milano
*10:50-11:15	Snapdragon Platform for High Performance 5G Mobile SOC & Al/Computing Application Manufactured with 4nm EUV Fin-FET Technology and Beyond
	Jun Yuan, Qualcomm
*11:15-11:40	Large Scale VLSI Mask Optimization
	Bei Yu, The Chinese University of Hong Kong
11:40-11:55	Universal Process Migration Solution of MAGICAL for Analog IC Layout Automation
	Yufeng Wei, Fudan University
11:55-13:30	Lunch Break
Session V: Al Inc	novations in Semiconductor Manufacturing
Session Chair: Y	•
*13:30-13:55	Deep Neural Network Proxy Modelling for IC Virtual Fabrication
	Dong Ni, Zhejiang University
13:55-14:10	A SelectiveNet-based Method for Defect Classification in Semiconductor Manufacturing
	Qian Jin, Zhejiang University
14:10-14:25	Al driven process control by machine learning based virtual metrology for high product mix manufacturing
	Chunshan Du, Siemens EDA
14:25-14:40	Machine Learning Technologies for Semiconductor Manufacturing
	LiFei Sun, Lam Research
14:40-14:55	Deep-Learning-Based Proxy Modeling for Microscopic Process of Plasma Etching
	Shuhang Chen, Zhejiang University
14:55-15:10	Predicting Material Removal Rate in Chemical Mechanical Polishing (CMP) Using
14.00 10.10	Explainable Machine Learning Methods
15:10-15:25	Jiahui Zuo, Zhejiang University  Coffee Break
15:10-15:25	Coffee Break
Consider VIII Adve	and manufacture Commission director Materials and Davisso
Session VI: Adva	ancements in Semiconductor Materials and Devices Dong Ni
*15:25-15:50	Research on the application of artificial intelligence in device compact model and
10.20 10.00	technology – circuits co-optimization
*45.50 40.45	Ye Lu, Fudan University
*15:50-16:15	Vector Matrix Multiplication with Two-Dimensional Materials
	Mario Lanza, KAUST α-In <sub>2</sub> Se <sub>3</sub> /MoTe <sub>2</sub> heterojunction for p-type junction field-effect transistors with ferroelectric
16:15-16:30	memory characteristics
	Tianjiao Zhang, Zhejiang University
16:30-16:45	Investigation of the Carrier Velocity in Short Channel Ge MOSFET with NiGe Metal
	Source/Drain Jing Yan, Zhejiang University
16:45-17:00	A First-Principles Study on the Stable Phase in Yttrium-Doped HfO₂
10.70 17.00	Xiaomin Xiao, Peking University
17:00-17:15	Tiny Neural Network Representing MOSFET Physical Effect Sub-model
	Shuhan Wang, Peking University

Poster Session: High-speed performance testing strategy and solution for Al wave

Zhexi Yan, ADVANTEST

Metal-Oxide-Metal Capacitor Simulation and Modeling by Virtual Fabrication

Qingpeng Wang, Lam Research

APPLICATION OF ADVANCED PROCESS CONTROL FOR IC MANUFACTURING

Linglie Zeng, Ontoinnovation

Study of Defectivity and Yield Impact from the Establishment and Optimization of FOUP Clean and FOUP Use Routine in Advanced IC Manufacturing

Zhigang Zhang, Brooks Technology (Shanghai) Limited

**Anomaly Detection of CDSEM Images** 

Meng Xue, Shanghai Huali Microelectronics Corporation

PMOS leakage reduction through SiGe morphology & IMP profile fine tune

WenZhao Fu, Shanghai Huali Integrated Circuit Corporation

The Defect Formation and Reduction of 55NM Ultra-low Power (55ULP) BEOL Process

Qing Mao, Shanghai Huali microelectronics Corporation

A Novel GAN-based Data Augmentation Algorithm for Semiconductor Defect Inspection

Lilei Hu, Shanghai University

Simulation and study of the interaction between needle mark morphology and probe card

Chenxi Zhao, Shanghai Huali integrated Circuit Manufacturing Co., Ltd.

CONVOLUTIONAL NEURAL NETWORK (CNN) BASED PROCESS WINDOW ANALYSISING FOR LITHOGRAPHY

Zeyang Chen, School of Micro-Nano Electronics, Zhejiang University

Structure Optimization of NOR Flash for Improving Cell Performance

Jiayu Ma, Shanghai Huali Integrated Circuit Corporation

Improved EM Performance by Adjusting Etching Profile of Top Metal for 28HK Metal Gate Process

Zherui Cao, Shanghai Huali Integrated Circuit Co., Ltd.

Digitalization Solutions for Automated Material Handling Systems in Semiconductor Smart Factories

Ruiji Wang, Huaxin (Jiaxing) Intelligent Equipment Co., Ltd.

High-Performance of SOT-MRAM Based on Optimization of Integration Processes

Xiaofei FAN, Truth Memory Corporation

A novel deep neural network based algorithm for fast wafer effective carrier lifetime measurement using heterodyne lock-in carrierography

Lilei Hu, Shanghai University

A method for predicting the film thickness of IC deposited films based on FCBF-CatBoost

Cai Yu, University of Science and Technology of China

55NM ULTRA LOW LEAKAGE PLATFORM DEVELOPMENT

Yifan Ding, Shanghai Huali Microelectronics Corporation

High Performance Wafer Defect Classification Model Based on Feature Fusion and RGB SEM images

Zhongyu Shi, University of Science and Technology of China

DSA for Nickel Silicide Formation in Advanced Devices

Haifeng Zhu, Applied Materials

Surface Damage Matching between VIISta 550H and VIISta 1500H

Huang Zeng, Applied Materials

**Model of Organic Ferroelectric Transistors for Neural Networks** 

Kairui Ding, Nanjing University of Posts and Telecommunications